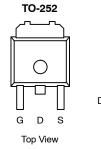


SUD40N08-16 N-Channel 80 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (A)	
80	0.016 @ V _{GS} = 10 V	40	

FEATURES

- TrenchFET® Power MOSFET
- 175°C Maximum Junction Temperature
- 100% Rg Tested



Drain Connected to Tab

G O F

Ordering Information:

SUD40N08-16 SUD40N08-16—E3 (Lead Free)

N-Channel MOSFET

D

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter		Limit	Unit			
Drain-Source Voltage		80				
Gate-Source Voltage		±20	- V			
$T_{C} = 25^{\circ}C$	- I _D	40				
$T_C = 125^{\circ}C$		30				
Pulsed Drain Current		60	А			
Continuous Source Current (Diode Conduction)		40				
Avalanche Current		40				
L = 0.1 mH	E _{AR}	80	mJ			
$T_{C} = 25^{\circ}C$	_	136 ^b				
$T_A = 25^{\circ}C$	PD	3 ^a	w			
Operating Junction and Storage Temperature Range			°C			
	$T_{C} = 25^{\circ}C$ $T_{C} = 125^{\circ}C$ $L = 0.1 \text{ mH}$ $T_{C} = 25^{\circ}C$	$\begin{tabular}{ c c c c } \hline & & & & & & \\ \hline & & & & & & \\ \hline & & & &$	$\begin{tabular}{ c c c c } \hline $Symbol & Limit \\ \hline V_{DS} & 80 \\ \hline V_{GS} & ± 20 \\ \hline V_{GS} & ± 20 \\ \hline $V_{C} = 25^{\circ}C$ & I_{D} & 40 \\ \hline $T_{C} = 125^{\circ}C$ & I_{D} & 60 \\ \hline $T_{C} = 125^{\circ}C$ & I_{D} & 60 \\ \hline I_{S} & 40 \\ \hline I_{S} & 40 \\ \hline I_{AR} & 40 \\ \hline I_{AR} & 40 \\ \hline $I_{C} = 25^{\circ}C$ & I_{AR} & 80 \\ \hline $T_{A} = 25^{\circ}C$ & P_{D} & 136^{b} \\ \hline $T_{A} = 25^{\circ}C$ & P_{D} & 3^{a} \\ \hline \end{tabular}$			

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
	$t \le 10 \text{ sec}$	R _{thJA}	15	18	°C/W		
Junction-to-Ambient ^a	Steady State		40	50			
Junction-to-Case		R _{thJC}	0.85	1.1			

Notes

a. Surface Mounted on 1" x1" FR4 Board.

b. See SOA curve for voltage derating.



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Parameter	Symbol	Test Condition	Min	Тур ^а	Max	Unit
Static			•			1
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I_D = 250 μ A	80			- v
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\;\mu A$	2.0		4.0	
Gate-Body Leakage	I _{GSS}	$V_{DS}=0~V,~V_{GS}=~\pm~20~V$			±100	nA
Zero Gate Voltage Drain Current		$V_{DS} = 80 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			1	
	I _{DSS}	V_{DS} = 80 V, V_{GS} = 0 V, T_{J} = 125 °C			50	μΑ
		V_{DS} = 80 V, V_{GS} = 0 V, T_{J} = 175 $^{\circ}$ C			250	
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	60			Α
		V_{GS} = 10 V, I _D = 40 A		0.013	0.016	
Drain-Source On-State Resistance ^b	r _{DS(on)}	V_{GS} = 10 V, I_{D} = 40 A, T_{J} = 125 $^{\circ}C$			0.027	Ω
		V_{GS} = 10 V, I_{D} = 40 A, T_{J} = 175 $^{\circ}C$			0.037	
Forward Transconductance ^b	9fs	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 40 \text{ A}$		45		S
Dynamic ^a					•	
Input Capacitance	C _{iss}			1960		pF
Output Capacitance	C _{oss}	V_{GS} = 0 V, V_{DS} = 25 V, F = 1 MHz		370		
Reverse Transfer Capacitance	C _{rss}			200		
Total Gate Charge ^c	Qg			42	60	
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 40 V, V_{GS} = 10 V, I_{D} = 40 A		7		nC
Gate-Drain Charge ^c	Q _{gd}			13		
Gate Resistance	Rg		0.5		2.7	Ω
Turn-On Delay Time ^c	t _{d(on)}			12	20	ns
Rise Time ^c	tr	Vpp = 40 V. Rι = 1.0 Ω		52	80	
Turn-Off Delay Time ^c	t _{d(off)}	$\begin{array}{l} V_{DD}$ = 40 V, R_L = 1.0 $\Omega \\ I_D \cong \mbox{ 40 A, } V_{GEN}$ = 10 V, R_g = 2.5 $\Omega \end{array}$		25	38	
Fall Time ^c	t _f			10	15	
Source-Drain Diode Ratings and	d Characteristi	c (T _C = 25°C)		•	•	
Pulsed Current	I _{SM}				60	А
Diode Forward Voltage ^b	V _{SD}	$I_F = 40 \text{ A}, V_{GS} = 0 \text{ V}$		1.0	1.5	V
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 40 A, di/dt = 100 A/µs		45	70	ns

Notes

a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
c. Independent of operating temperature.

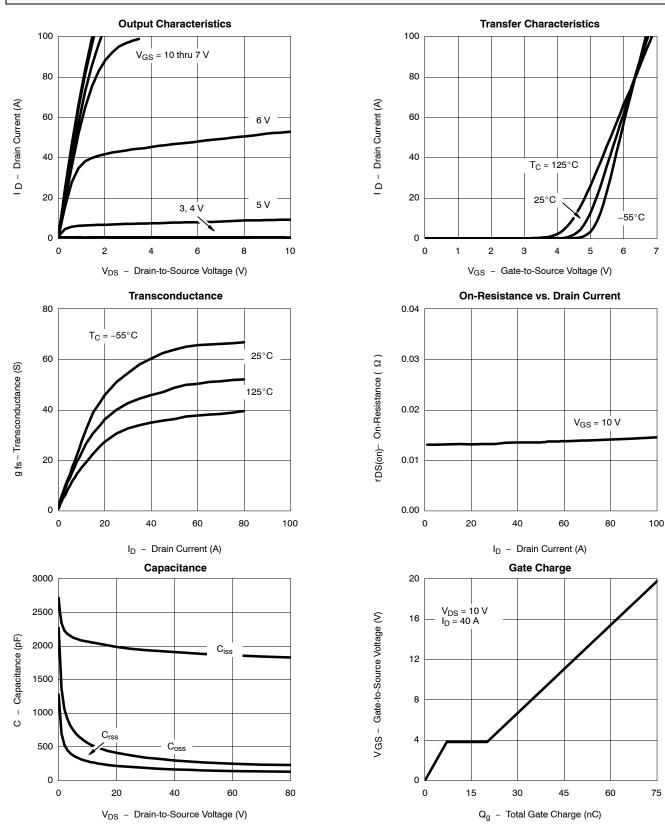


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TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



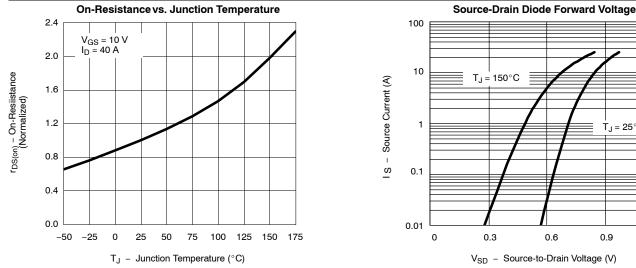


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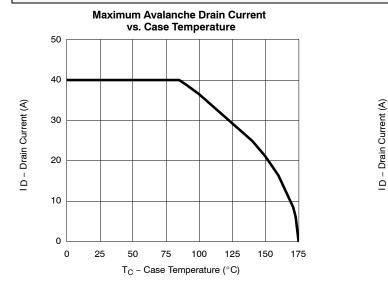
N-Channel

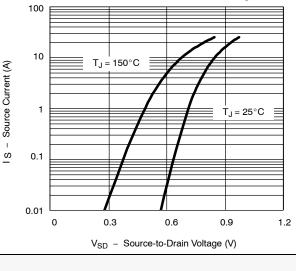
80 V (D-S) 175 °C MOSFET

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



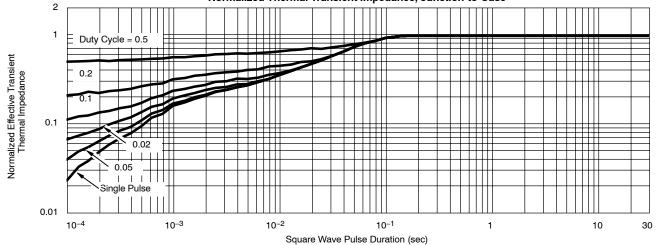
THERMAL RATINGS





Safe Operating Area 1000 100 10 µs Limited by r_{DS(on)} H . 100 μs 10 1 ms 10 ms 100 ms 1 $T_C = 25^{\circ}C$ ≡1 s, dc Single Pulse 0.1 0.1 1 10 100 V_{DS} - Drain-to-Source Voltage (V)







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